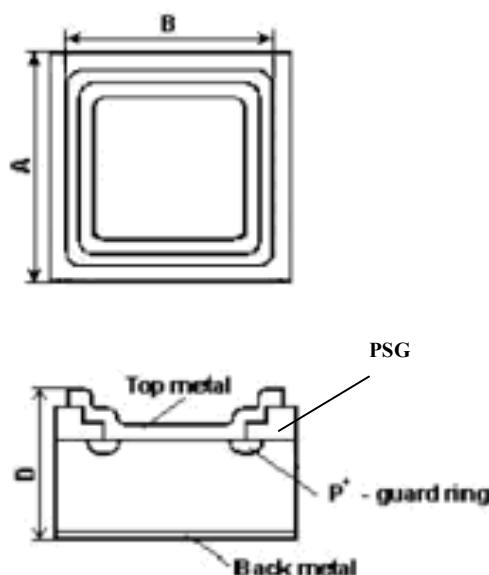


SCHOTTKY DIODES. KDS-03040F.
PRELIMINARY

May. 2013.

VSP-MIKRON	3A/40V. Die Size-51mil.			
Electrical Characteristics	Symbol	Unit	Spec. limit	Die Sort
Breakdown Voltage @ $I_R=10\text{mA}$	V_B	V	40	45
Average Rectified Forward Current	$I_{F(AV)}$	A	3,0	-
DC Forward Voltage @ 25°C , $I_F=3,0\text{A}$	V_F	V	0,45	0,43
Maximum Reverse Current @ 25°C , $V_R=45\text{V}$ @ 25°C , $V_R=40\text{V}$ @ 100°C , $V_R=40\text{V}$	I_R	MA	- 0,70 50,0	0,70 0,50 40,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	I_{FSM}	A	60	-
Peak Repetitive Reverse Surge Current @ $2,0\mu\text{s}$, $f=1\text{kHz.}$, $T_J < 150^\circ\text{C.}$	I_{RRM}	A	2,0	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	ESD	kV	± 8 (contact)	
Voltage Rate of Change	dV/dt	V/ μS	10.000	
Operating Junction Temperature	T_J	°C	125	



DIM	ITEM	µm
A_x	Die Size	1300
A_y		1300
B_x	Top Metal Size	1112
B_y		1112
D	Thickness	250max.
	Scribe line Width	80

Top metal: a) Al – for Wire Bonding;
b) Al-Ni-Ag – for Soldering.
Backside metal: Ti-Ni-Ag.